



30V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(on)}	Ι _D T _A = +25°C
201/	$0.15\Omega @ V_{GS} = -10V$	-2.6A
-30V	$0.23\Omega @ V_{GS} = -4.5V$	-1.5A

Description

This MOSFET utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed, making it ideal for high-efficiency power management applications.

Applications

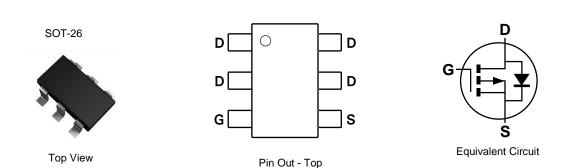
- DC-DC Converters
- Power Management Functions
- Disconnect Switches
- Motor Control

Features and Benefits

- Fast Switching Speed
- Low On-Resistance
- Low Threshold
- Low Gate Drive
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT-26
- Case Material: Molded Plastic; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish; Solderable per MIL-STD-202, Method 208 3
- Weight: 0.015 grams (Approximate)



Ordering Information (Note 4)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXM62P03E6TA	2P03	7	8	3,000 Units
ZXM62P03E6TC	2P03	13	8	10,000 Units

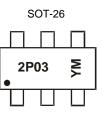
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



 $\begin{array}{l} 2\text{P03}=\text{Product Type Marking Code}\\ \text{YM}=\text{Date Code Marking}\\ \text{Y or }\overline{Y}=\text{Year (ex: C=2015)}\\ \text{M or }\overline{M}=\text{Month (ex: 9=September)} \end{array}$

Notes:

Date Code Rey												
Year	2015		2016	2017		2018	2019		2020	2021		2022
Code	С		D	E		F	G		Н	I		J
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Cł	naracteristic		Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	-30	V
Gate-Source Voltage			V _{GS}	±20	V
Continuous Drain Current	V _{GS} = -4.5V	T _A = +25°C (Note 5) T _A = +70°C (Note 5)	ID	-1.5 -1.2	А
Pulsed Drain Current (Note 7	7)		I _{DM}	-7.4	А
Continuous Source Current (Body Diode)		Is	-0.54	А
Pulsed Source Current (Bod	y Diode)		I _{SM}	-7.4	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	Р	625	mW
Linear Derating Factor	PD	5	mW/°C
Power Dissipation (Note 6)		806	mW
Linear Derating Factor	PD	6.4	mW/°C
Thermal Resistance, Junction to Ambient (Note 5)	R _{0JA}	113	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	73	°C/W
Operating and Storage Temperature Range	T _{J,} T _{STG}	-55 to +150	°C

Notes:

5. For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions 6. For a device surface mounted on FR4 PCB measured at t \leq 5 seconds.

7. Repetitive rating - pulse width limited by maximum junction temperature. Refer to Transient Thermal Impedance graph.

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	-30			V	$I_D = -250 \mu A, V_{GS} = 0 V$
Zero Gate Voltage Drain Current	IDSS	_	_	-1	μA	$V_{DS} = -30V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}	_		±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(th)}	-1			V	$I_D = -250 \mu A$, $V_{DS} = V_{GS}$
Static Drain-Source On-Resistance (Note 8)	D			0.15	Ω	$V_{GS} = -10V, I_D = -1.6A$
	R _{DS (ON)}			0.23	12	$V_{GS} = -4.5V, I_D = -0.8A$
Forward Transconductance (Notes 8 & 10)	g _{fs}	1.1			S	$V_{DS} = -10V, I_D = -0.8A$
Diode Forward Voltage (Note 8)	V _{SD}	_		-0.95	V	$T_J = +25^{\circ}C, I_S = -1.6A, V_{GS} = 0V$
Reverse Recovery Time (Note 10)	t _{rr}	_	19.9		ns	T _J = +25°C, I _F = -1.6A,
Reverse Recovery Charge (Note 10)	Q _{rr}	_	13		nC	di/dt = 100A/µs
DYNAMIC CHARACTERISTICS (Note 10)						
Input Capacitance	C _{iss}	_	330			
Output Capacitance	Coss	_	120		pF	V _{DS} = -25V, V _{GS} = 0V f = 1.0MHz
Reverse Transfer Capacitance	C _{rss}	_	45			
Turn-On Delay Time (Note 9)	t _{d(on)}	_	2.8			
Turn-On Rise Time (Note 9)	tr	_	6.4		ns	$V_{DD} = -15V, I_D = -1.6A,$
Turn-Off Delay Time (Note 9)	t _{d(off)}	_	13.9		ns	$R_G \cong 6.2\Omega, R_D \cong 25\Omega,$
Turn-Off Fall Time (Note 9)	t _f		10.3]	
Total Gate Charge (Note 9)	Qg	_		10.2		N 041/ 1/ 401/
Gate-Source Charge (Note 9)	Q _{gs}	_		1.5	nC	$V_{DS} = -24V, V_{GS} = -10V,$
Gate-Drain Charge (Note 9)	Q _{gd}			3	1	I _D = -1.6A

8. Measured under pulsed conditions. Pulse width = 300μ s. Duty cycle $\leq 2\%$.

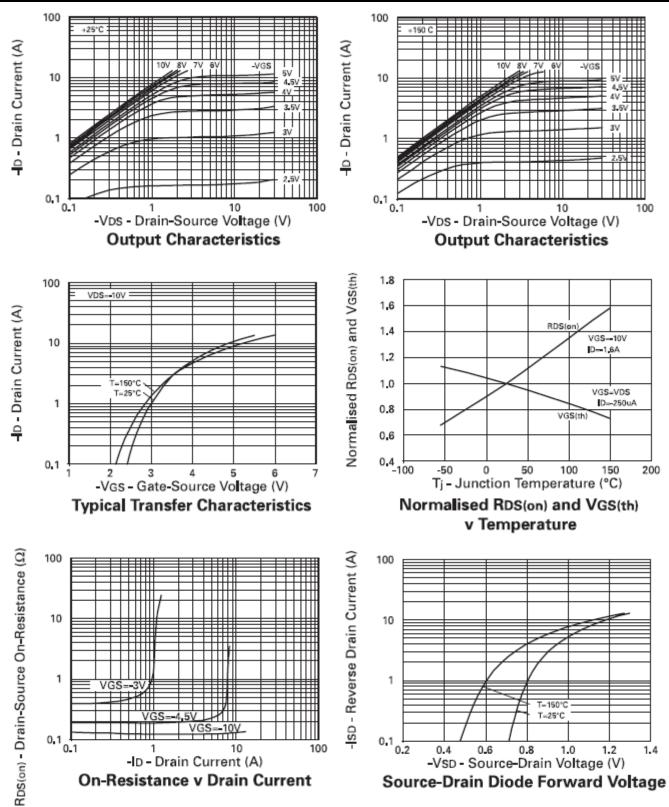
9. Switching characteristics are independent of operating junction temperature.

10. For design aid only, not subject to production testing.

Notes:

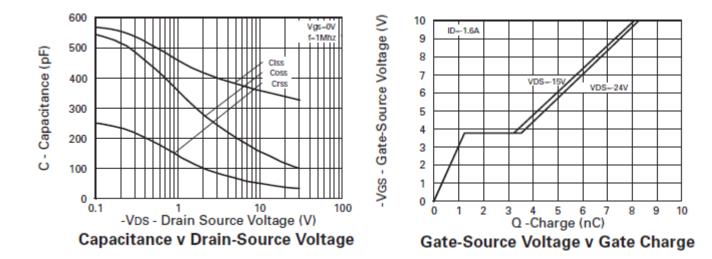


Typical Characteristics

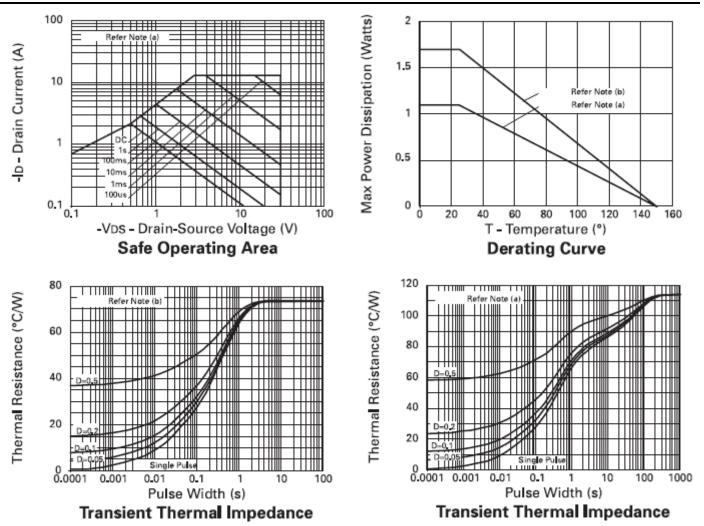




Typical Characteristics (cont.)

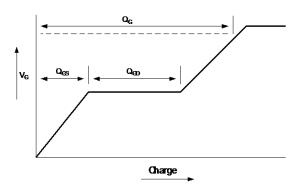


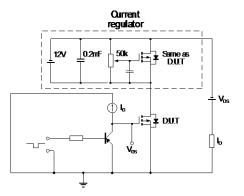
Thermal Characteristics





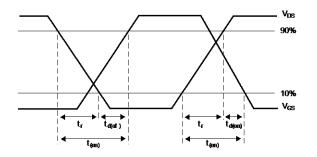
Test Circuits



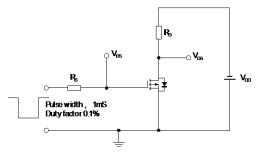


Basic gate charge waveform





Switching time waveforms

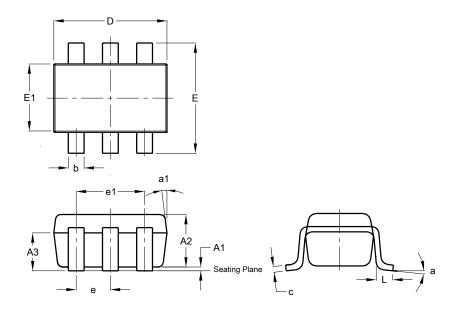


Switching time test circuit



Package Outline Dimensions

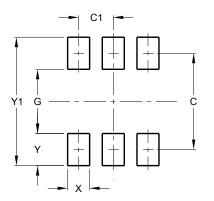
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT26							
Dim	Min	Max	Тур				
A1	0.013	0.10	0.05				
A2	1.00	1.30	1.10				
A3	0.70	0.80	0.75				
b	0.35	0.50	0.38				
С	0.10	0.20	0.15				
D	2.90	3.10	3.00				
е	-	-	0.95				
e1	-	-	1.90				
Е	2.70	3.00	2.80				
E1	1.50	1.70	1.60				
L	0.35	0.55	0.40				
а	-	-	8°				
a1	-	-	7°				
All Dimensions in mm							

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.40
C1	0.95
G	1.60
Х	0.55
Y	0.80
Y1	3.20



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